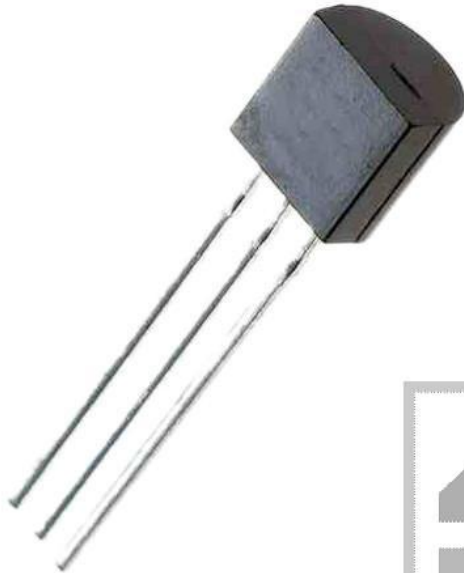




TR 2N2222A;CDIL;TO92; tranzystor; NPN;800mA;75V;500mW;300MHz;Pbf



Dane techniczne:

Nazwa: 2N2222A

Typ tranzystora: bipolarny

Kierunek przewodnictwa: NPN

Prąd kolektora: 0,8A

Napięcie kolektor-emiter: 75V

Moc: 500mW

Częstotliwość: 300MHz

Obudowa: TO92


Montaż: przewlekany (THT)

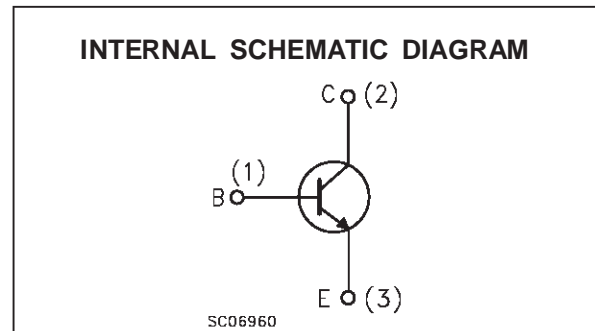
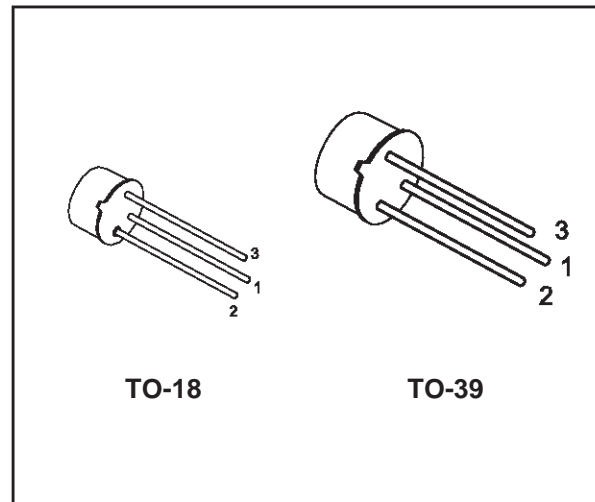
Producent: CDIL

HIGH SPEED SWITCHES

DESCRIPTION

The 2N2219A and 2N2222A are silicon planar epitaxial NPN transistors in Jedec TO-39 (for 2N2219A) and in Jedec TO-18 (for 2N2222A) metal case. They are designed for high speed switching application at collector current up to 500mA, and feature useful current gain over a wide range of collector current, low leakage currents and low saturation voltage.

 2N2219A approved to CECC 50002-100,
2N2222A approved to CECC 50002-101
available on request.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	75	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	40	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	6	V
I_C	Collector Current	0.8	A
P_{tot}	Total Dissipation at $T_{amb} \leq 25^\circ\text{C}$ for 2N2219A for 2N2222A at $T_{case} \leq 25^\circ\text{C}$ for 2N2219A for 2N2222A	0.8	W
		0.5	W
		3	W
		1.8	W
T_{stg}	Storage Temperature	-65 to 200	$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	175	$^\circ\text{C}$

THERMAL DATA

			TO-39	TO-18	
$R_{thj-case}$	Thermal Resistance Junction-Case	Max	50	83.3	$^{\circ}C/W$
$R_{thj-amb}$	Thermal Resistance Junction-Ambient	Max	187.5	300	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current ($I_E = 0$)	$V_{CB} = 60 V$ $V_{CB} = 60 V$ $T_{case} = 150^{\circ}C$			10 10	nA μA
I_{CEX}	Collector Cut-off Current ($V_{BE} = -3V$)	$V_{CE} = 60 V$			10	nA
I_{BEX}	Base Cut-off Current ($V_{BE} = -3V$)	$V_{CE} = 60 V$			20	nA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = 3 V$			10	nA
$V_{(BR)CBO}^*$	Collector-Base Breakdown Voltage ($I_E = 0$)	$I_C = 10 \mu A$	75			V
$V_{(BR)CEO}^*$	Collector-Emitter Breakdown Voltage ($I_B = 0$)	$I_C = 10 mA$	40			V
$V_{(BR)EBO}^*$	Emitter-Base Breakdown Voltage ($I_C = 0$)	$I_E = 10 \mu A$	6			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = 150 mA$ $I_B = 15 mA$ $I_C = 500 mA$ $I_B = 50 mA$			0.3 1	V V
$V_{BE(sat)}^*$	Base-Emitter Saturation Voltage	$I_C = 150 mA$ $I_B = 15 mA$ $I_C = 500 mA$ $I_B = 50 mA$	0.6		1.2 2	V V
h_{FE}^*	DC Current Gain	$I_C = 0.1 mA$ $V_{CE} = 10 V$ $I_C = 1 mA$ $V_{CE} = 10 V$ $I_C = 10 mA$ $V_{CE} = 10 V$ $I_C = 150 mA$ $V_{CE} = 10 V$ $I_C = 500 mA$ $V_{CE} = 10 V$ $I_C = 150 mA$ $V_{CE} = 1 V$ $I_C = 10 mA$ $V_{CE} = 10 V$ $T_{amb} = -55^{\circ}C$	35 50 75 100 40 50 35		300	
h_{fe}^*	Small Signal Current Gain	$I_C = 1 mA$ $V_{CE} = 10 V$ $f = 1KHz$ $I_C = 10 mA$ $V_{CE} = 10 V$ $f = 1KHz$	50 75		300 375	
f_T	Transition Frequency	$I_C = 20 mA$ $V_{CE} = 20 V$ $f = 100 MHz$	300			MHz
C_{EBO}	Emitter Base Capacitance	$I_C = 0$ $V_{EB} = 0.5 V$ $f = 100KHz$			25	pF
C_{CBO}	Collector Base Capacitance	$I_E = 0$ $V_{CB} = 10 V$ $f = 100 KHz$			8	pF
$R_{e(hie)}$	Real Part of Input Impedance	$I_C = 20 mA$ $V_{CE} = 20 V$ $f = 300MHz$			60	Ω

* Pulsed: Pulse duration = 300 μs , duty cycle $\leq 1\%$

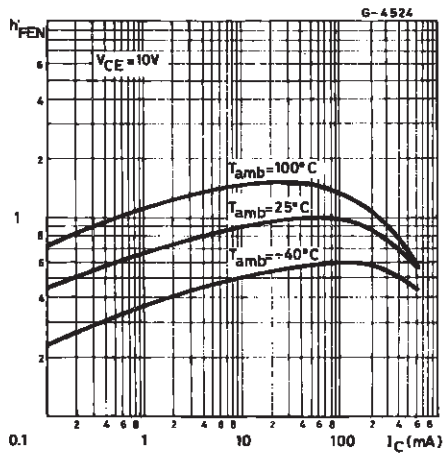
ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
NF	Noise Figure	$I_C = 0.1 \text{ mA}$ $V_{CE} = 10 \text{ V}$ $f = 1\text{KHz}$ $R_g = 1\text{K}\Omega$		4		dB
h_{ie}	Input Impedance	$I_C = 1 \text{ mA}$ $V_{CE} = 10 \text{ V}$ $I_C = 10 \text{ mA}$ $V_{CE} = 10 \text{ V}$	2 0.25		8 1.25	$\text{k}\Omega$ $\text{k}\Omega$
h_{re}	Reverse Voltage Ratio	$I_C = 1 \text{ mA}$ $V_{CE} = 10 \text{ V}$ $I_C = 10 \text{ mA}$ $V_{CE} = 10 \text{ V}$			8 4	10^{-4} 10^{-4}
h_{oe}	Output Admittance	$I_C = 1 \text{ mA}$ $V_{CE} = 10 \text{ V}$ $I_C = 10 \text{ mA}$ $V_{CE} = 10 \text{ V}$	5 25		35 200	μS μS
t_d^{**}	Delay Time	$V_{CC} = 30 \text{ V}$ $I_C = 150 \text{ mA}$ $I_{B1} = 15 \text{ mA}$ $V_{BB} = -0.5 \text{ V}$			10	ns
t_r^{**}	Rise Time	$V_{CC} = 30 \text{ V}$ $I_C = 150 \text{ mA}$ $I_{B1} = 15 \text{ mA}$ $V_{BB} = -0.5 \text{ V}$			25	ns
t_s^{**}	Storage Time	$V_{CC} = 30 \text{ V}$ $I_C = 150 \text{ mA}$ $I_{B1} = -I_{B2} = 15 \text{ mA}$			225	ns
t_f^{**}	Fall Time	$V_{CC} = 30 \text{ V}$ $I_C = 150 \text{ mA}$ $I_{B1} = -I_{B2} = 15 \text{ mA}$			60	ns
r_{bb} , $C_{b'c}$	Feedback Time Constant	$I_C = 20 \text{ mA}$ $V_{CE} = 20 \text{ V}$ $f = 31.8\text{MHz}$			150	ps

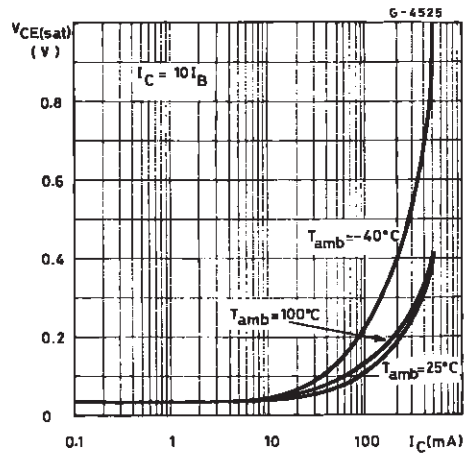
* Pulsed: Pulse duration = 300 μs , duty cycle $\leq 1\%$

** See test circuit

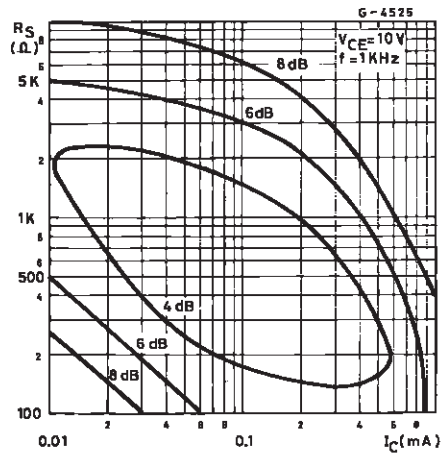
Normalized DC Current Gain.



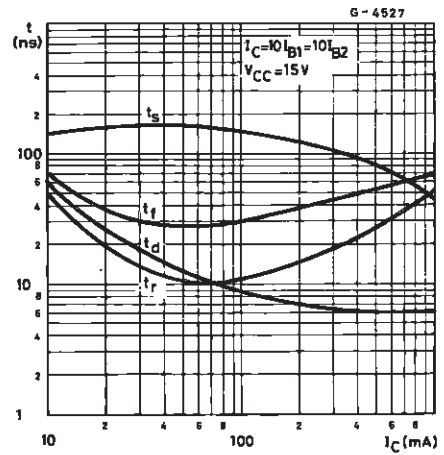
Collector-emitter Saturation Voltage.



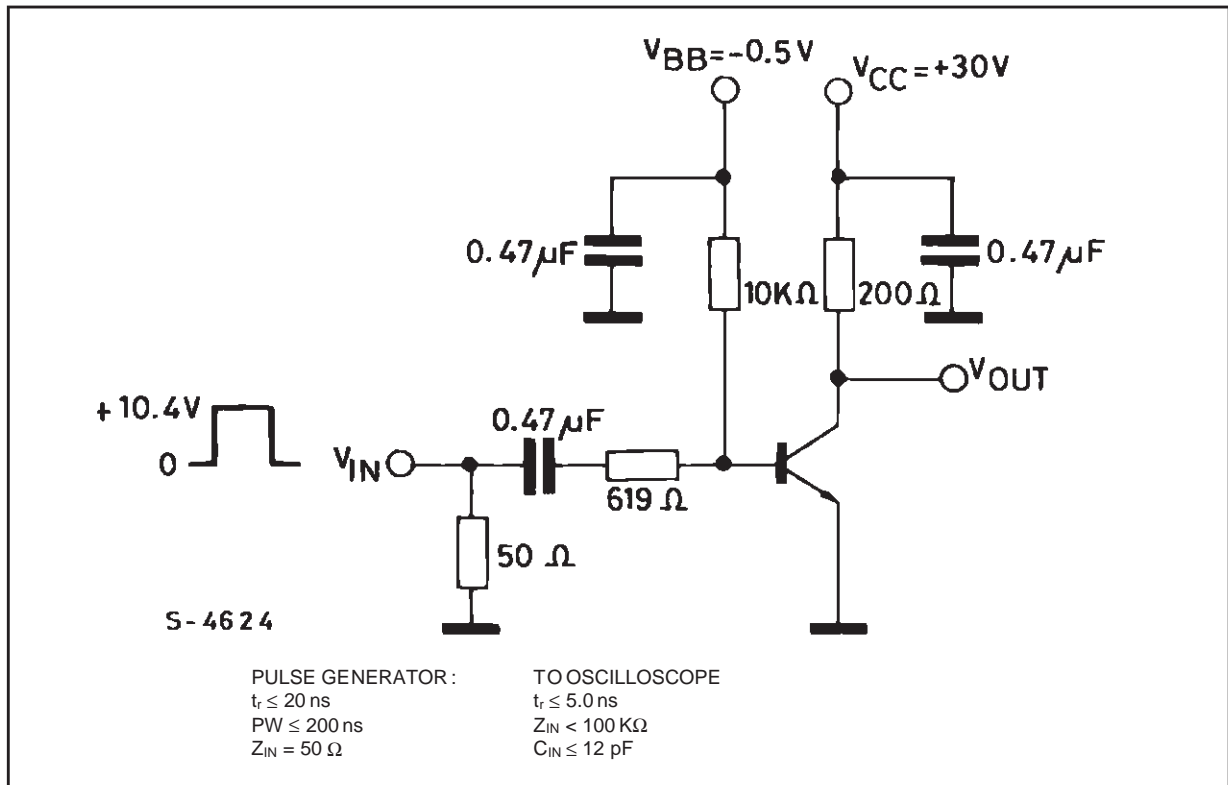
Contours of Constant Narrow Band Noise Figure.



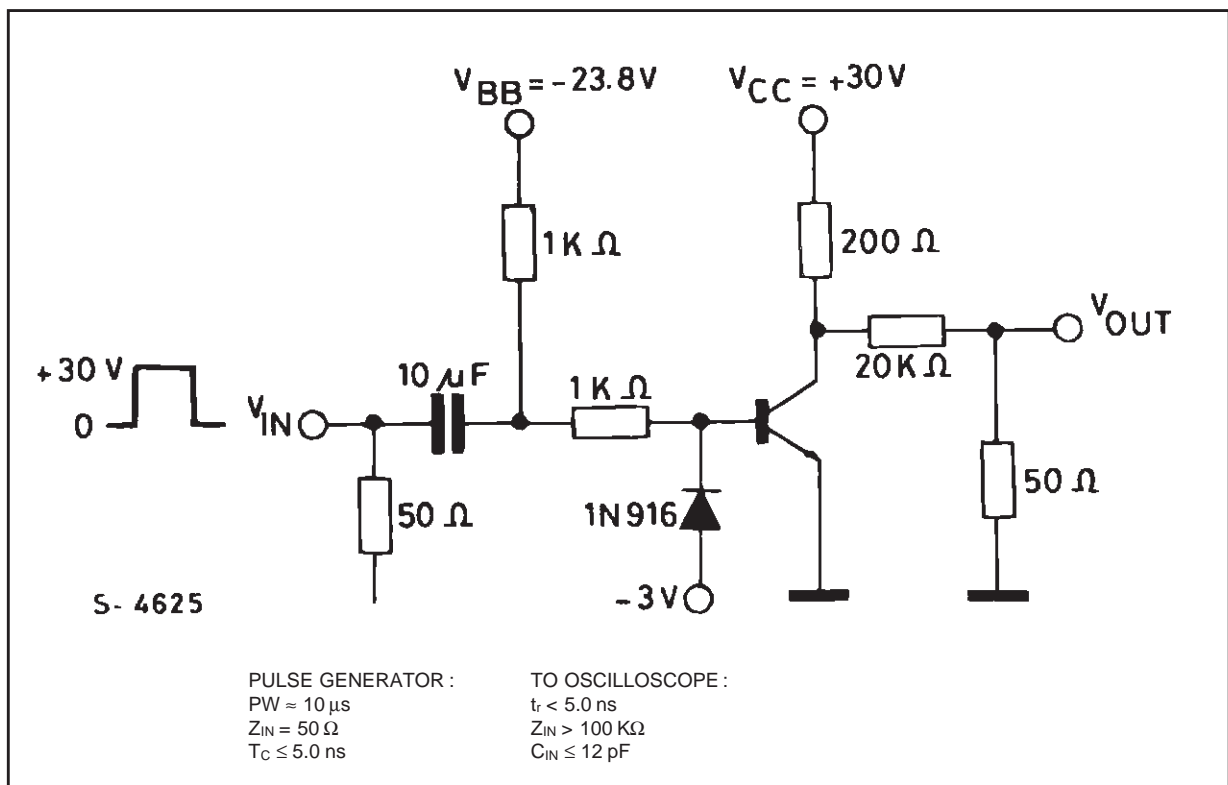
Switching Time vs. Collector Current.



Test Circuit for t_d , t_r .

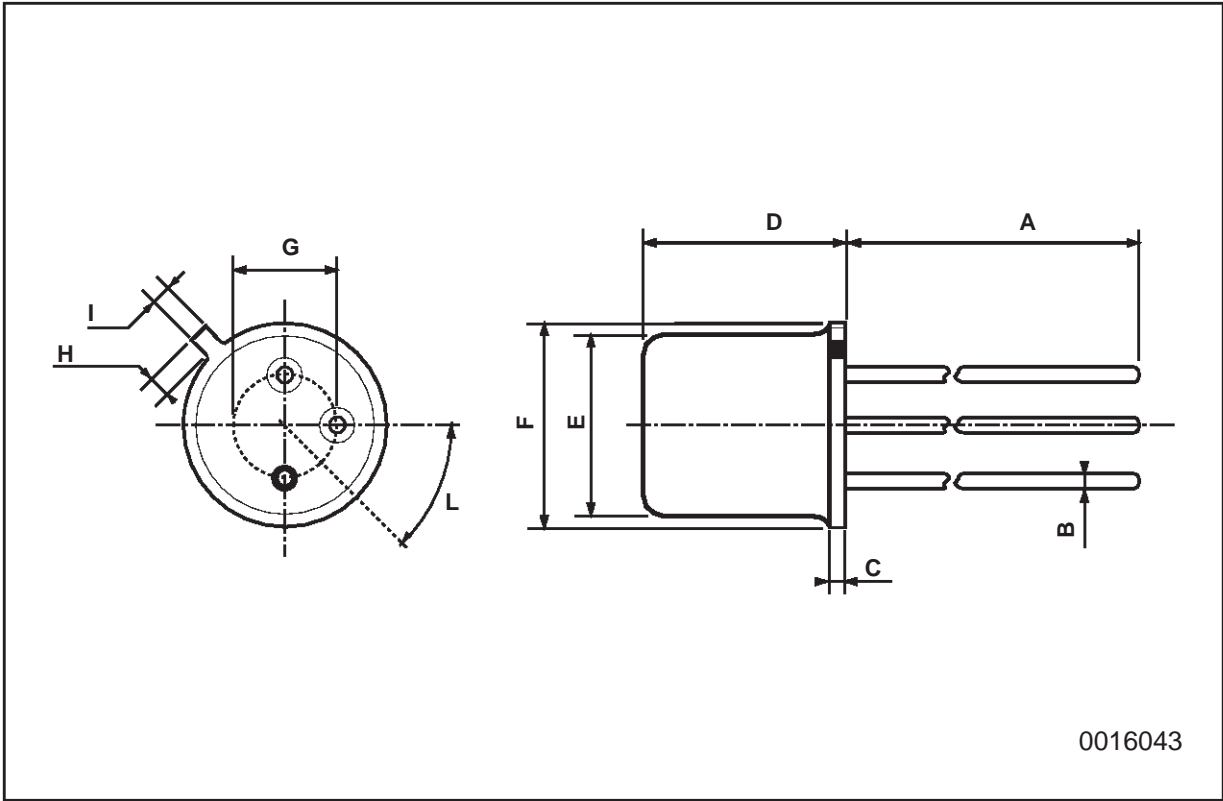


Test Circuit for t_d , t_r .



TO-18 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A		12.7			0.500	
B			0.49			0.019
D			5.3			0.208
E			4.9			0.193
F			5.8			0.228
G	2.54			0.100		
H			1.2			0.047
I			1.16			0.045
L	45°			45°		

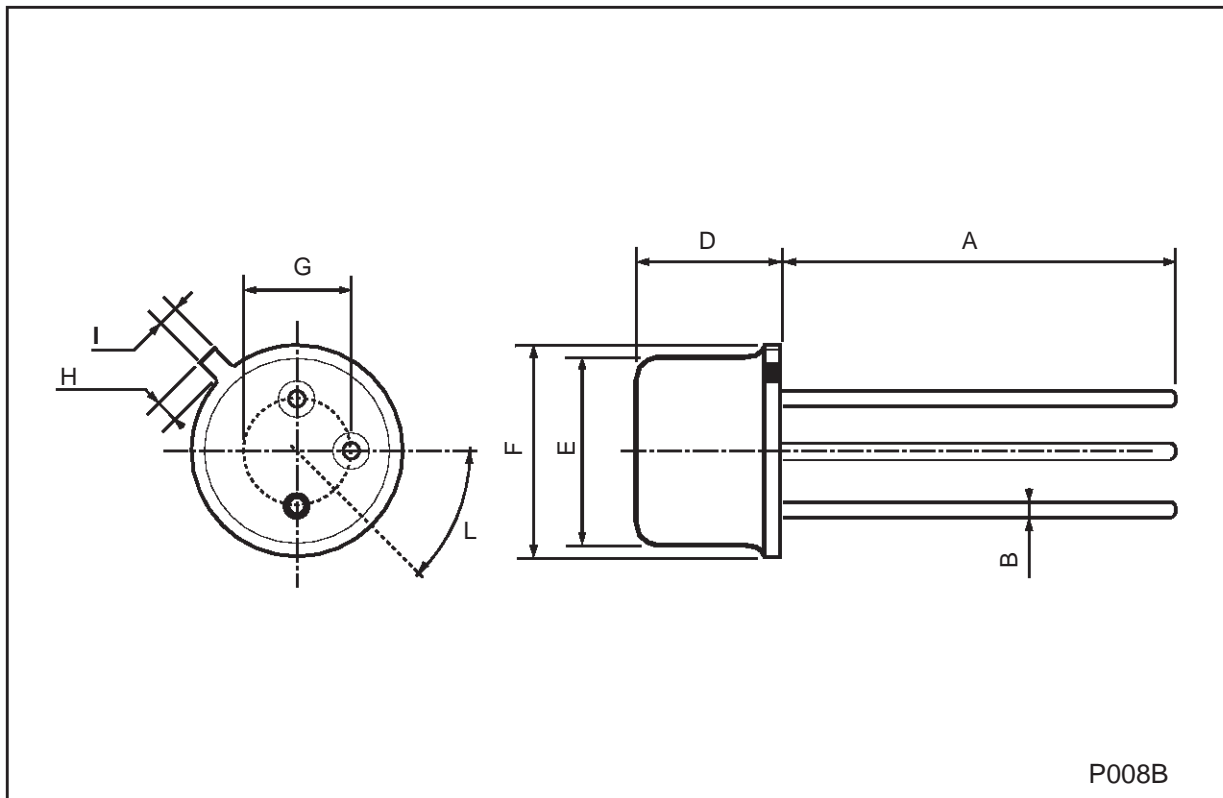


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TO-39 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	12.7			0.500		
B			0.49			0.019
D			6.6			0.260
E			8.5			0.334
F			9.4			0.370
G	5.08			0.200		
H			1.2			0.047
I			0.9			0.035
L	45° (typ.)					



P008B

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